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REFERENCE DES	SIGNATION	U.S. PATENT D	OCUMENTS		
EXAMINER DOCUMENT NUMBER		DATE	NAME	CLASS/ SUBCLASS	FILING DATE

## EXAMINER INITIAL DOCUMENT DATE COUNTRY SUBCLASS YES NO

EXAMINER INITIAL		OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)					
UK	A1	"64M x 8 Bit NAND Flash Memory," Samsung Electronics (October 27, 2000).					
UR	A2	"How Flash Memory Works," wysiwyg://8/http://www.howstuffworks.com/flash-memory.htm?printable=1, 5 pages (1998).					
4/2	A3	"Datalight FlashFX™ 4.06 User's Guide," page 11 (August 2000).					
ur	A4	"How Does TrueFFS® manage Wear Leveling?," <a href="http://www.m-sys.com/content/information/calcInfo.asp">http://www.m-sys.com/content/information/calcInfo.asp</a> , 2 pages (printed October 5, 2001)					

COPY OF PAPERS ORIGINALLY FILED

EXAMINER	Kevia	L.,	Ellis	DATE CONSIDERED	5/23	/03

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

(use several sheets if necessary)

SERIAL NO.

09/972,787

FILING DATE
October 5, 2001

APPLICANT(S): Friedman et al.

REFERENCE	DESIG	GNATION	U.S. PATE	NT DOCUMENTS		
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
UR	A1	5,414,829	05/1995	Fandrich et al.		

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EXAMINER Kevin L. Ellis DATE CONSIDERED 5/23/03

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Rev. Dec.-99

AUG 2 2 2002		#1
FORM TO-1448	SERIAL NO. 09/972,787	CASE NO. 10519/37
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE October 5, 2001	GROUP ART UNIT 2185
(use several sheets if necessary)	APPLICANT(S): Friedman et al.	

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING	
UR	A1	6,181,603	01/30/2001	Jyouno et al.			
NR	A2	6,034,882	03/07/2000	Johnson et al.		AUG 2 6	<u> </u>
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NR	A14	"A 125mm² 1Gb NAND Flash Memory with 10MB/s Program Throughput," Nakamura et al., ISSCC 2002/Session 6/SRAM and Non-Volatile Memories/6.4, 2002 IEEE International Solid-State Circuits Conference, Digest of Technical Papers, pages 106-107 (2002).			
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KE	A16	"NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell," Eitan et al., IEEE Electron Device Letters, Vol. 21, No. 11, pages 543-545 (November 2000).			
uk	A17	"A 512Mb NROM Flash Data Storage Memory with 8MB/s Data Rate," Maayan et al., ISSCC 2002/Session 6/SRAM and Non-Volatile Memories/6.1, 2002 IEEE International Solid-State Circuits Conference, Digest of Technical Papers, pages 100-101 (2002).			
UR	A18	"Ovonic Unified Memory – A High-Performance Nonvolatile Memory Technology for Stand- Alone Memory and Embedded Applications," Gill et al., ISSCC 2002/Session 12/TD Digital Directions/12.4, 2002 IEEE International Solid-State Circuits Conference, Digest of Technical Papers, pages 202-203 (2002).			
nk	A19	"0.13 µm Metal-Oxide-Nitride-Oxide-Semiconductor Single Transistor Memory Cell with Separated Source Line," Fujiwara et al., Jpn. J. Appl. Phys. Vol. 39, pp. 417-423, Part 1, No. 2A (February 2000).			
UR	A20	"Three-Dimensional Memory Array and Method of Fabrication," U.S. Patent Application Serial No. 09/560,626, filing date 04/28/2000, inventor: N. Johan Knall.			

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Page 2 of 2

1	FORM PTO-1449	SERIAL NO.	CASE NO.
	PROMIT 10-1440	09/972,787	10519/37
1/	LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE October 5, 2001	GROUP ART UNIT 2185
•	(use several sheets if necessary)	APPLICANT(S): Friedman et al.	

EXAMINER INITIAL		OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)
UR	A21	"Digital Memory Method and System for Storing Multiple-Bit Digital Data," U.S. Patent Application Serial No. 09/932,701, filing date 08/17/2001, inventors: Michael A. Vyvoda and N. Johan Knall.
NR	A22	"Memory Device and Method for Reliably Reading Multi-Bit Data from a Write-Many Memory Cell," U.S. Patent Application Serial No. 10/144,451, filing date 5/9/02, inventor: Bendik Kleveland.



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FORM PTO-1449	SERIAL NO.	CASE NO.
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LIST OF PATENTS AND PUBLICATIONS FOR	FILING DATE	GROUP ART UNIT
APPLICANT'S INFORMATION DISCLOSURE	. October 5, 2001	2185
STATEMENT		
(use several sheets if necessary)	APPLICANT(S): Friedman et al.	

REFERENCE DESIGNATION				U.S. PATENT DOCUMENTS			
F	EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
L	MITIAL		HOMBER	DAIL	11/2016	OCEOLAGO	<u> </u>
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